

SANYO Semiconductors DATA SHEET

LV5761V — 1-channel Step-down Switching Regulator

Overview

The LV5761V is a 1-channel step-down switching regulator.

Functions

- 1 channel step-down switching regulator controller.
- Frequency decrease function at pendent.
- Load-independent soft start circuit.
- ON/OFF function.
- Built-in pulse-by-pulse OCP circuit. It is detected by using ON resistance of an external MOS.
- Synchronous rectification.
- Current mode control.
- Synchronous drive by external signal.

Specifications

Absolute Maximum Ratings at Ta = 25°C

Parameter	Symbol	Conditions	Ratings	Unit
supply voltage	V _{IN} max		45	V
Allowable Power dissipation	Pd max	Mounted on a specified board. *	0.74	W
Operating temperature	Topr		-40 to +85	°C
Storage temperature	Tstg		-55 to +150	°C

^{*} Specified board: 114.3mm × 76.1mm × 1.6mm, glass epoxy board

Recommended Operating Range at Ta = 25°C

	Parameter	Symbol	Conditions	Ratings	Unit
	Supply voltage range	V_{IN}		8.5 to 42	V
ſ	Error amplifier input voltage			0 to 1.6	V

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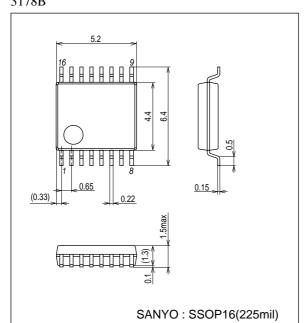
LV5761V

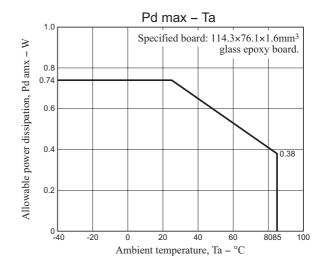
Electrical Characteristics at Ta = 25 °C, $V_{\mbox{\footnotesize{IN}}} = 12V$

Parameter	Symbol Conditions	Ratings			Unit	
Parameter	Symbol	Conditions	min	typ	max	Unit
Reference voltage block	•					
Internal reference voltage	Vref	Including offset of E/A	0.654	0.67	0.686	V
5V power supply	V_{DD}	I _{OUT} = 0 to 5mA	4.7	5.2	5.7	V
Triangular waveform oscillator blo	ock					
Oscillation frequency	Fosc	$RT = 220k\Omega$	110	125	140	kHz
Frequency variation	Fosc DV	V _{IN} = 8 to 42V		1		%
Oscillation frequency fold back detection voltage	VOSC FB	FB voltage detection after SS ends		0.1		V
Oscillatory frequency after fold back	FOSC FB			1/3F _{OSC}		kHz
ON/OFF circuit block						
IC start-up voltage	V _{EN} on		2.5	3.0	3.5	V
IC off voltage	V _{EN} off		1.0	1.2	1.4	V
Soft start circuit block						
Soft start source current	I _{SS} SC	EN > 3.5V	4	5	6	μА
Soft start sink current	I _{SS} SK	EN < 1V, V _{DD} = 5V		2		mA
UVLO circuit block						
UVLO lock release voltage	V _{UVLO}		7.5	8.0	8.5	V
UVLO hysteresis	V _{UVLO} H			0.7		V
OCP circuit block				•	•	
OCP charge current	locp			5		μΑ
Error amplifier	•	•			'	
Input bias current	IEA IN				100	nA
Error amplifier transconductance	G _{EA}		1000	1400	1800	μΑ/V
Sink output current	IEA OSK	FB = 1.0V		-100		μΑ
Source output current	I _{EA} OSC	FB = 0V		100		μА
Current detection amplifier gain	GISNS			1.5		
over current limiter circuit block	1	1				
Reference current 1	I _{LIM} 1	MODE = L (GND)	-10%	18.5	+10%	μΑ
Reference current 2	I _{LIM} 2	MODE = H (V _{IN})	-10%	37.0	+10%	μΑ
Over current detection comparator offset voltage	VLIM OFS		-5		+5	mA
Over current detection comparator common mode input range			V _{IN} -0.45		V _{IN}	V
PWM comparator	•			· · · · · · · · · · · · · · · · · · ·		
Input threshold voltage	Vt max	Duty cycle = DMAX	0.9	1.0	1.1	V
(fosc = 125kHz)	Vt0	Duty cycle = 0%	0.4	0.5	0.6	V
Maximum ON duty	DMAX		80	85	90	%
Output block	•	•			'	
Output stage ON resistance (the upper side)	RONH			5		Ω
Output stage ON resistance (the under side)	R _{ONL}			5		Ω
Output stage ON current (the upper side)	IONH		240			mA
Output stage ON current (the under side)	IONL		240			mA
The whole device	1	•	L	i I		
Standby current	Iccs	EN < 1V			10	μА
Mean consumption current	ICCA	EN > 3V		3		mA

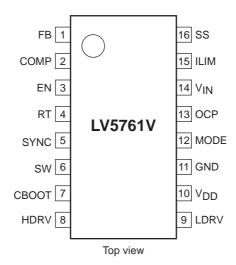
Package Dimensions

unit: mm (typ) 3178B

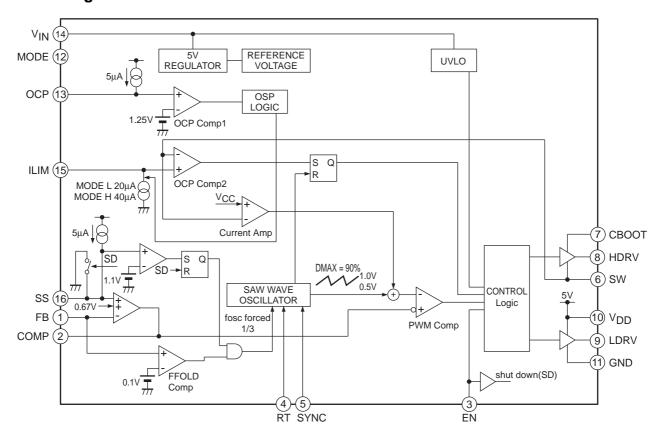




Pin Assignment



Block Diagram



Pin Function

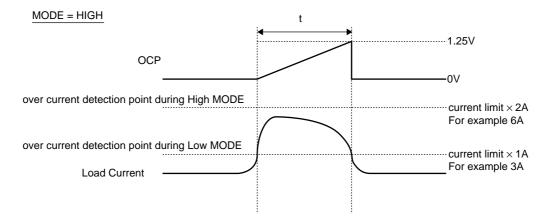
Pin No.	Pin name	Description		
14	VIN	Power supply pin. This pin is monitored by UVLO function. When the voltage of this pin becomes 8V or more by UVLO function The IC starts and the soft start function operates.		
11	GND	Ground pin. Each reference voltage is based on the voltage of the ground pin.		
10	V_{DD}	Power supply pin for an external the lower MOS-FET gate drive.		
7	CBOOT	Bootstrap capacity connection pin. This pin becomes a GATE drive power supply of an external NchMOSFET. Connect a bypath capacitor between CBOOT and SW.		
6	SW	Pin to connect with switching node. The source of NchMOSFET connects to this pin.		
5	SYNC	External synchronous signal input pin.		
9	LDRV	An external the lower MOSFET gate drive pin.		
8	HDRV	An external the upper MOSFET gate drive pin.		
1	FB	Error amplifier reverse input pin. By operating the converter, the voltage of this pin becomes 0.67V. The voltage in which the output voltage is divided by an external resistance is applied to this pin. Moreover, when this pin voltage becomes 0.1V or less after a soft start ends, the oscillatory frequency becomes 1/3.		
2	COMP	Error amplifier output pin. Connect a phase compensation circuit between this pin and GND.		
16	SS	Pin to connect a capacitor for soft start. A capacitor for soft start is charged by using the voltage of about 5μA. This pin ends the soft start period by using the voltage of about 1.1V and the frequency fold back function becomes active.		
15	ILIM	Reference current pin for current detection. The sink current of about $20\mu\text{A}$ flows to this pin when Low level (GND) is set to the MODE pin. Also, the sink current of about $40\mu\text{A}$ flows to this pin when High level (V _{IN}) is set to the MODE pin. When a resistance is connected between this pin and V _{IN} outside and the voltage applied to the SW pin is lower than the voltage of the terminal side of the resistance, the upper NchMOSFET is off by operating the current limiter comparator. This operation is reset with respect to each PWM pulse.		
3	EN	ON/OFF pin.		
13	OCP	Pin to set the time of the timer (during double the over current detection point) Connect a capacitor between this pin and GND. OCP charge current : 5µA		
4	RT	Pin to set the oscillation frequency. Connect a resistance between this pin and GND.		
12	MODE	Pin to switch the over current detection point. Set by the low level (GND) of the ILIM pin. Set by the high level (V _{IN}) of the OCP pin. When this MODE pin is set to the high level and the point of the over current detection is set by using the ILIM pin is exceeded, the value becomes double the original value. Also, when the MODE pin is set to the low level, the point of the over current detection remains an original value.		

Timing Chart

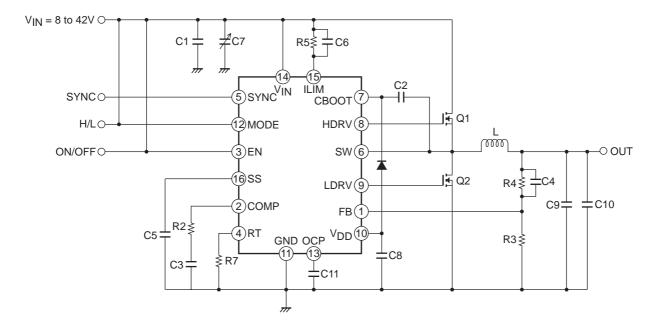
When the MODE pin is set to the high level and the point of the over current detection is set by using the ILIM pin is exceeded, the value becomes double the original value.

Also, when the MODE pin is set to the low level, the point of over current detection remains an original value.

Timing chart of the over current detection point switching is as below.



Sample Application Circuit



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